

**Amendments to the Specification:**

Please replace paragraph number 37 at page 9 with the following amended paragraph:

[0037] The resulting semiconductor device 100 illustrated in Fig. 10 has a silicon-oxide-nitride-oxide-silicon (SONOS) structure. That is, semiconductor device 100 may include a silicon pillar structure 210 with ONO dielectric layers 410-430 and a silicon control gate 510 formed thereon.

Pillar structures 210 function as a channel region or substrate electrode for the memory device and ONO layers ~~310-330~~ 410-430 may function as a charge storage structure.